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Docket No.: M-12524 US

September 18, 2002

missioner For Patents nington, D.C. 20231

Applicant(s):

Fortin, Vincent; Tsai, Kuei-Chang

Assignee:

Mosel Vitelic, Inc.

Title:

Cobalt Silicide Fabrication Methods That Use Protective Titanium

Layers

Serial No .:

10/056,154

Examiner: Docket No.: Lee, Hsien Ming M-12524 US

Filed: January 23, 2002

Group Art Unit: 2823

Dear Sir:

 \boxtimes

Transmitted herewith are the following documents in the above-identified application:

(1) Return Receipt Postcard;

(2) This Transmittal Letter (in duplicate);

(3) Amendment (7 pages);

(4) Information Disclosure Statement Under 37 CFR § 1.97 With Fee (2 pages in duplicate);

(5) PTO Form 1449 (1 page); and

(6) Copy of two cited references.

No additional fee is required.

CLAIMS AS AMENDED

		Claims Remaining After Amendment		Highest No. Previously Paid For		Present Extra		Rate		Additional Fee
Total (Claims	6	Minus	20	=	0	x	\$18.00	\$	0.00
Indepe Claims		1	Minus	3	=	0	х	\$84.00	\$	0.00
	Fee of depend	for the first filinent claims per applicat		more multiple					\$	
	Fee for F	Request for Extension	of Time						\$	
Total additional fee for this Amendment:									\$	_0.00
\boxtimes	Conditional Petition for Extension of Time: If an extension of time is required for timely filing of the enclosed document(s) after all papers filed with this transmittal have been considered, an extension of time is hereby requested.									
\boxtimes	Please charge our Deposit Account No. 19-2386 in the amount of								\$	0.00
Also, charge any additional fees required and credit any overpayment to our Deposit Account No. 19-2386.										÷
							1	otal:	\$	_0.00

EXPRESS MAIL LABEL NO.

EV 174 806 423 US

Respectfully submitted,

Michael Shenker

Attorney for Applicant(s)

Reg. No. 34,250



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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COMMISSIONER FOR PATENTS Washington, D.C. 20231

AMENDMENT

September 18.

San Jose, California

Dear Sir:

In reply to the Office Action dated August 14, 2002, please amend this application as follows (a version with markings to show changes made is given at the end):

IN THE SPECIFICATION

Please amend the paragraph 0028 as follows:

[0028] In one example, cobalt silicide is formed on the source lines of a flash memory array illustrated in Figs. 5-8. Some features of this memory are described in U.S. patent application no. 09/640,139 filed August 15, 2000 by Hsing Tuan et al., entitled "Nonvolatile Memory Structures and Fabrication Methods", incorporated herein by reference (now U.S. patent no. 6,355,524 issued March 12, 2002). Fig. 5 is a circuit diagram showing two columns of the array. Fig. 6 is a top view. Fig. 7A illustrates a cross section of the array along the line A-A in Fig. 6. Fig. 7B illustrates a cross section along the line B-B.

LAW OFFICES OF SKJERVEN MORRILL MacPHERSON LLP

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Please amend the paragraph 0040 as follows:

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